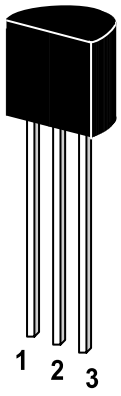
ST KSD471

NPN Silicon Epitaxial Planar Transistor
Audio Frequency Power amplifier applications.

The transistor is subdivided into three group, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25℃)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	^{O}C
Storage Temperature Range	T_S	-55 to +150	^{O}C

Characteristics at T_{amb}=25 ^{o}C

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE}=1V, I_C=100mA						
Current Gain Group	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
	G	h_{FE}	200	-	400	-
Collector Emitter Breakdown Voltage at I_C=10mA		$V_{(BR)CEO}$	30	-	-	V
Collector Base Breakdown Voltage at I_C=100μA		$V_{(BR)CBO}$	40	-	-	V
Emitter Base Breakdown Voltage at I_E=100μA		$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at V_{CB}=30V		I_{CBO}	-	-	0.1	μA
Collector Saturation Voltage at I_C=500mA, I_B=50mA		$V_{CE(sat)}$	-	-	0.5	V
Base Saturation Voltage at I_C=500mA, I_B=50mA		$V_{BE(sat)}$	-	-	1.2	V
Collector Output Capacitance at V_{CB}=6V, f=1MHz		C_{OB}	-	18	-	pF
Transition Frequency at V_{CE}=6V, I_C=10mA		f_T	-	130	-	MHz